



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



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## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	Q <sub>g</sub> Typ	I <sub>D</sub> T <sub>C</sub> = +25°C
40V	2.7mΩ @ V <sub>GS</sub> = 10V	68.6nC	100A

## Features


- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> – Minimizes Power Losses
- Low Q<sub>g</sub> – Minimizes Switching Losses

## Description and Applications

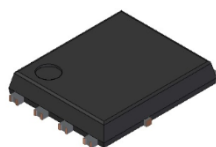
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters

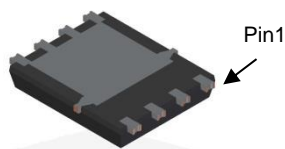
## Mechanical Data

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.097 grams (Approximate)

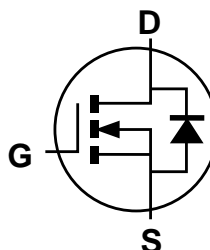
PowerDI5060-8/SWP (Type UX)



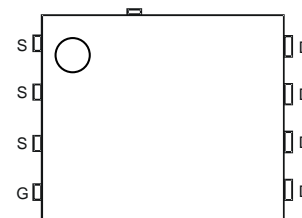
Top View



Bottom View



Internal Schematic



Top View  
Pin Configuration

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	40	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	I <sub>D</sub>	T <sub>A</sub> = +25°C	31
		T <sub>A</sub> = +70°C	26
Continuous Drain Current (Note 6)	I <sub>D</sub>	T <sub>C</sub> = +25°C	100
		T <sub>C</sub> = +100°C (Note 8)	100
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	350	A
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	100	A
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	350	A
Avalanche Current, L=0.2mH	I <sub>AS</sub>	45	A
Avalanche Energy, L=0.2mH	E <sub>AS</sub>	200	mJ

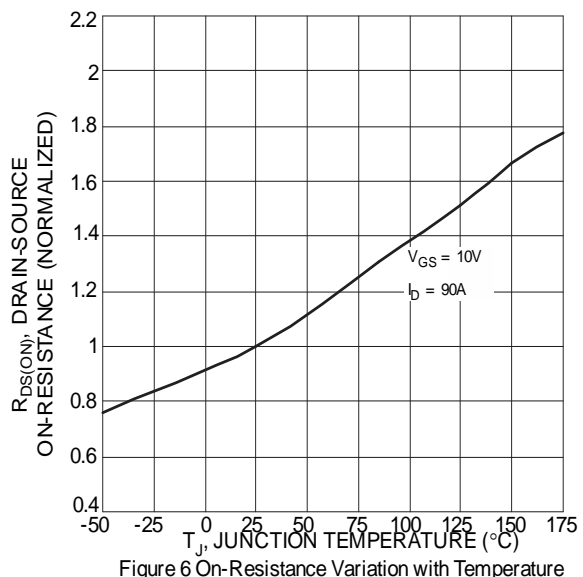
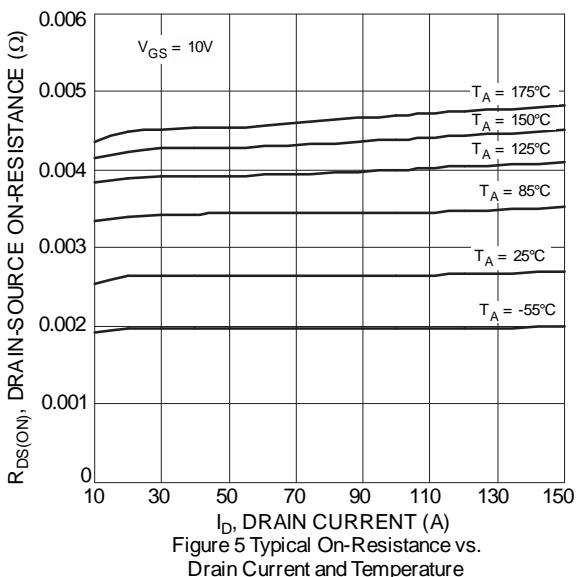
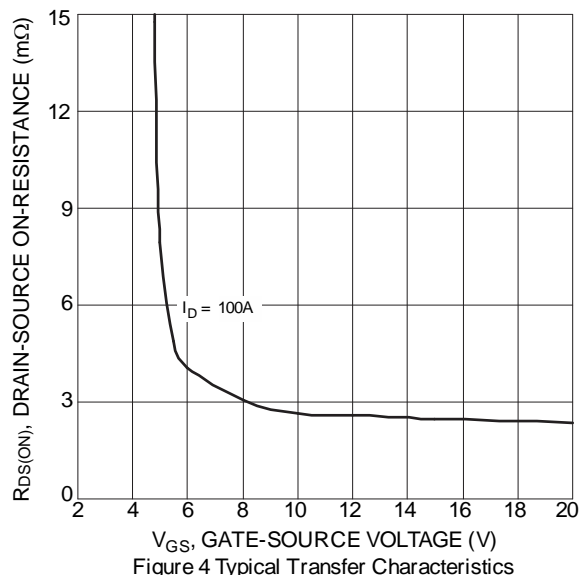
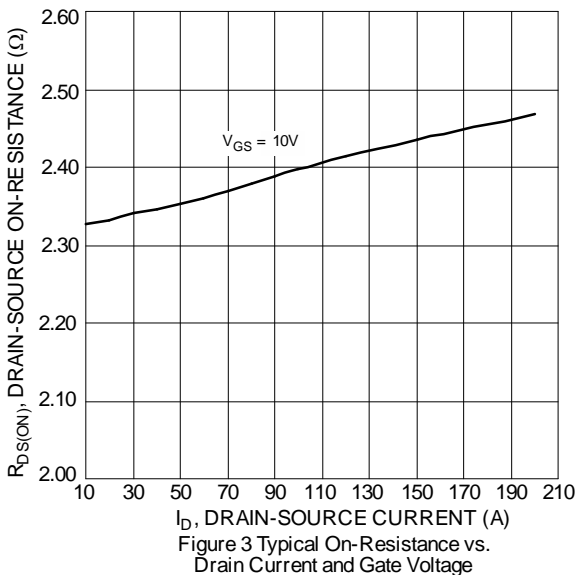
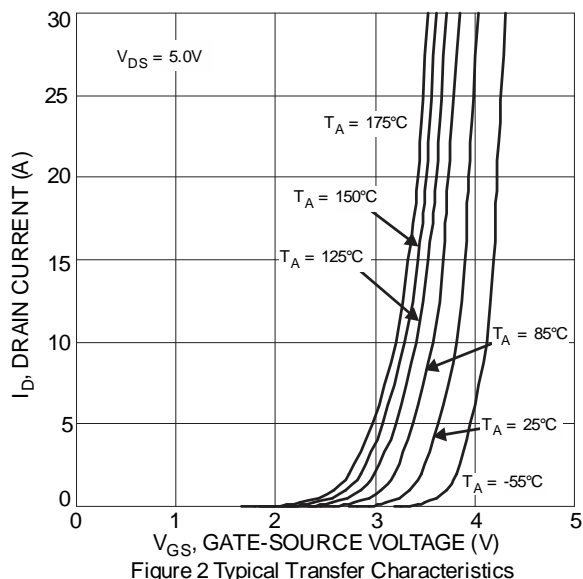
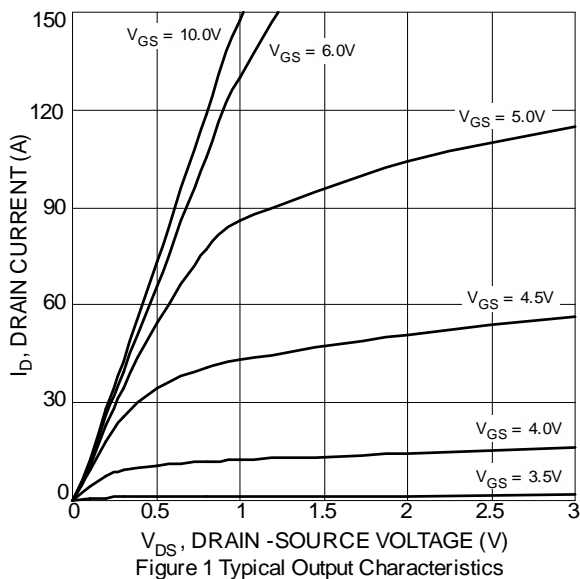
**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	3.6	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	41	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	167	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	0.9	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	2.3	2.7	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 90A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	4,305	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	1,441	—		
Reverse Transfer Capacitance	C <sub>riss</sub>	—	102	—		
Gate Resistance	R <sub>g</sub>	—	0.77	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	68.6	—	nC	V <sub>DD</sub> = 20V, I <sub>D</sub> = 90A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>gs</sub>	—	16.8	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	14.2	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	9.5	—	ns	V <sub>DD</sub> = 20V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 90A, R <sub>G</sub> = 3.5Ω
Turn-On Rise Time	t <sub>r</sub>	—	6.7	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	26.4	—		
Turn-Off Fall Time	t <sub>f</sub>	—	8.1	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	52.4	—	ns	I <sub>F</sub> = 50A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	78.2	—	nC	

- Notes:
- Device mounted with exposed drain pad on 25mm by 25mm 2oz copper on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady state.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing



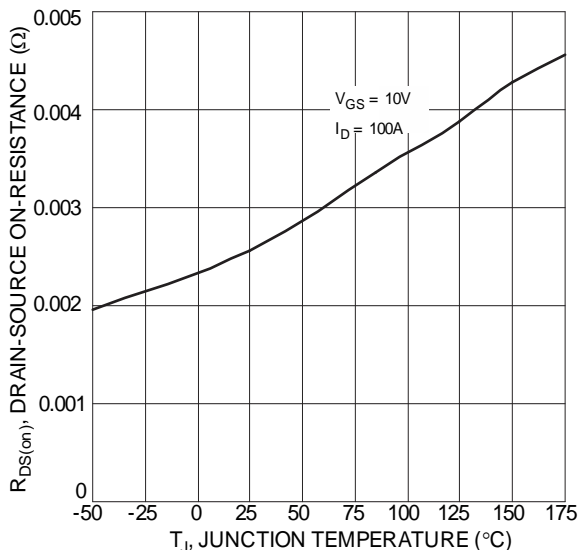


Figure 7 On-Resistance Variation with Temperature

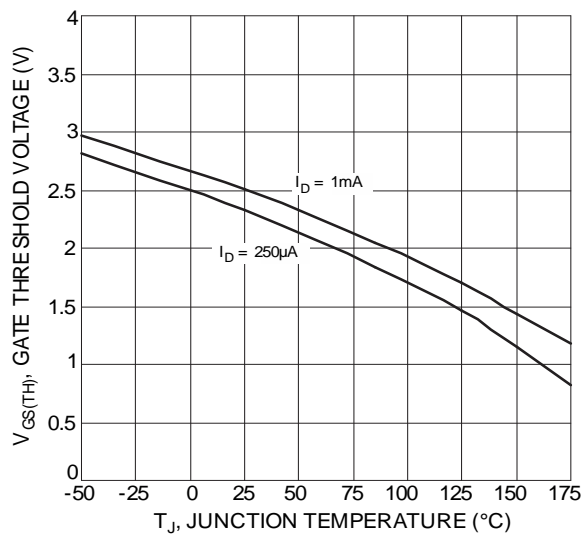


Figure 8 Gate Threshold Variation vs. Temperature

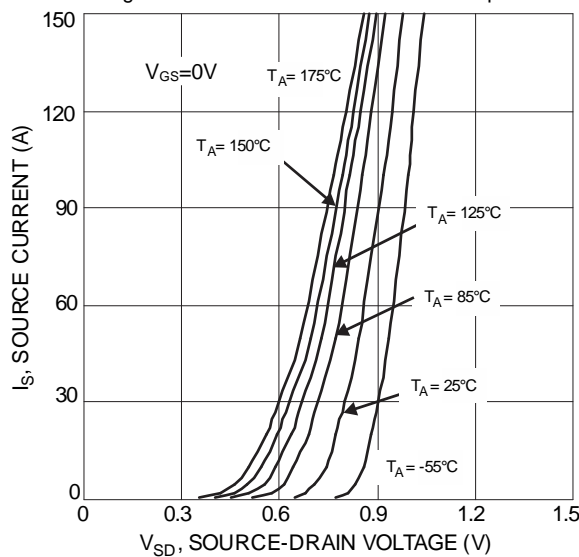


Figure 9 Diode Forward Voltage vs. Current

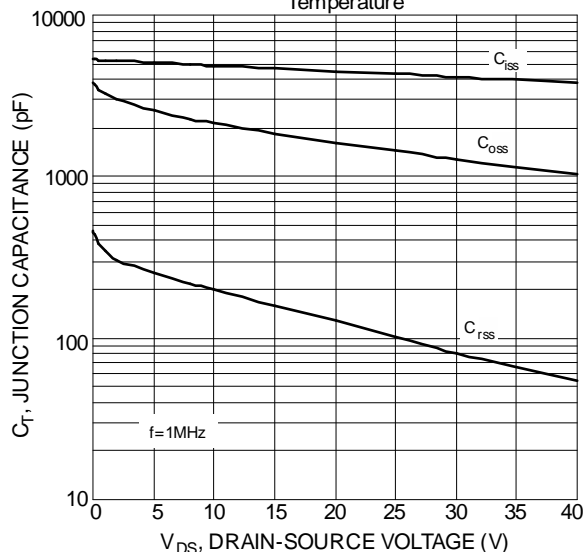


Figure 10 Typical Junction Capacitance

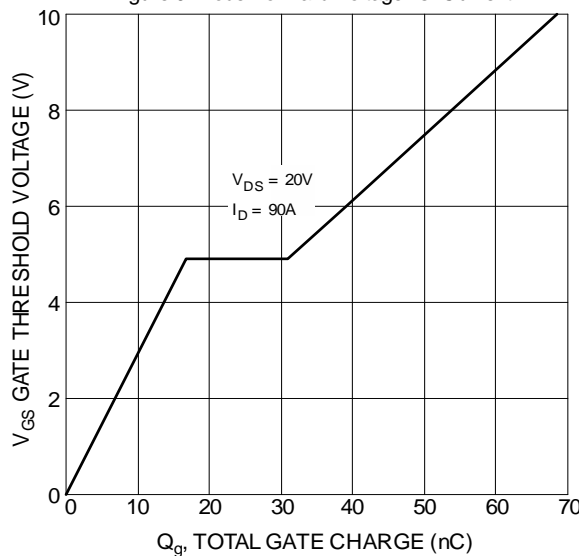


Figure 11 Gate Charge

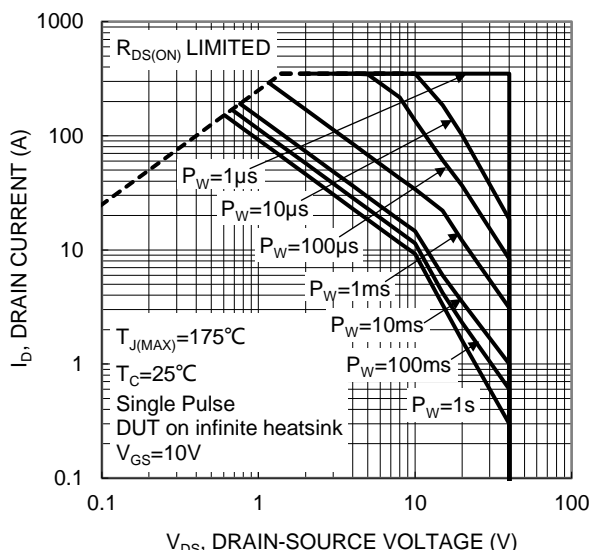
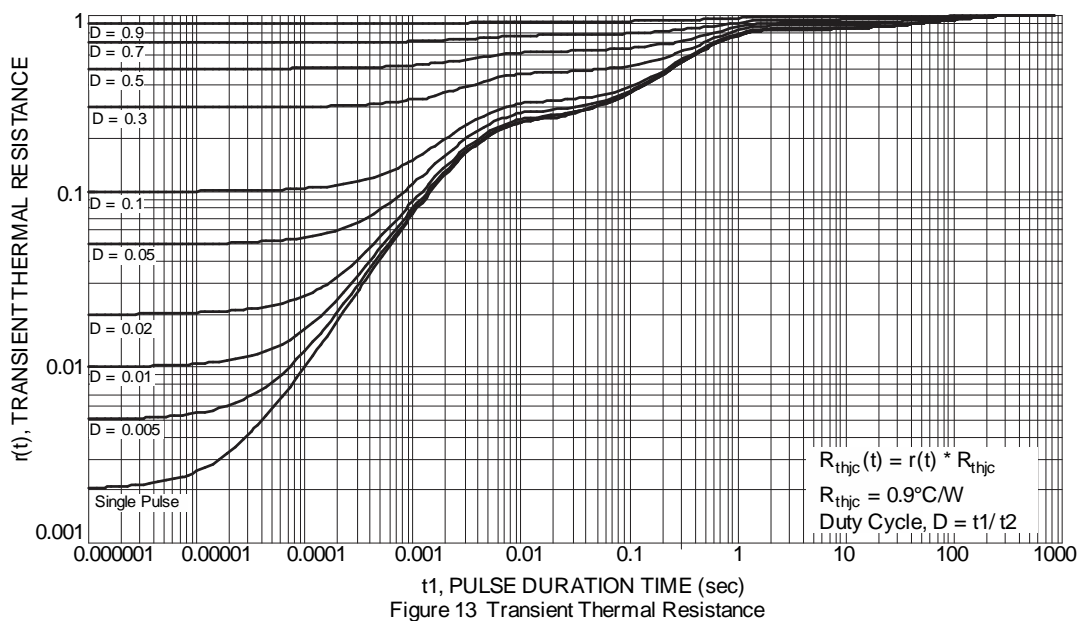
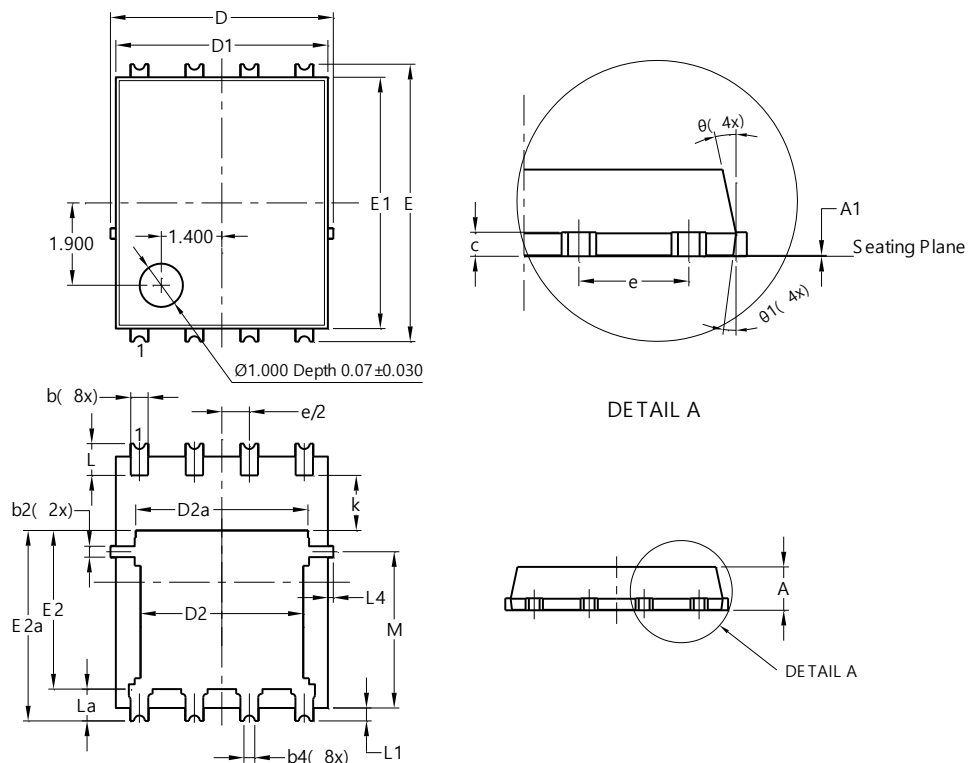


Figure 12. SOA, Safe Operation Area



### Package Outline Dimensions

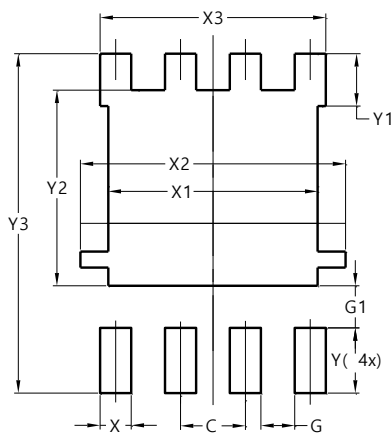
PowerDI5060-8/SWP (Type UX)



PowerDI5060-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

### Suggested Pad Layout

PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	5.190
X3	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610